

Crossover from 2D to 3D magnetic disorder in sub-mono-atomic ferromagnetic layers

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We present transport and magnetoresistance (MR) measurements performed on quench condensed ultrathin films of Gd evaporated on an amorphous Ge or Sb layer. These films show a large negative MR accompanied by a hysteretic superimposed structure. When the film is coated by an overlayer of Ge or Sb the magnitude of the MR increases and the hysteretic structure disappears. We speculate that the findings are a result of a crossover from a 2D magnetic disorder in the uncoated layers of Gd to a 3D magnetic disorder as the Gd film is coated by a semiconducting layer.

The magneto-transport properties of magnetic rare-earth atoms imbedded in a non-magnetic insulating matrix is a dramatic example of the effect of magnetic moments on the conductivity of semiconductors. Depending on the magnetic atom concentration, these systems can show extremely large magnetoresistance values [1, 2, 3]. In the case of three dimensional amorphous Gd-Si where the Gd ion has a spin $s=7/2$ it has been shown that the system can be continuously tuned through the metal-insulator transition [4]. The observed magnetic field driven transition from localized states subject to variable range hopping to extended states which show metallic behavior, was interpreted as being due to the extra degree of freedom added by the spin on the Gd. In the absence of magnetic field the Gd spin is randomly oriented and thus adds an additional disorder not experienced by a non-spin system [5]. With increasing magnetic field, the Gd spins are driven towards alignment, reducing the net disorder and thus increasing the conductivity. On the insulating side of the metal insulator transition, the magnetoresistance is spectacularly exponentially dependent on temperature and exceeds 5 orders of magnitude for a 10T field at $T<100\text{mK}$ [6].

In addition, tunneling and hall measurements were performed on these systems [7]. They show that the density of states (DOS) is substantially modified by the presence of magnetic field. For an insulating Gd-Si alloy in low field there are very few, if any, states available to tunnel into at the Fermi level. The tunneling conductance exhibits a strong voltage (energy) dependence demonstrating that this is a strongly coulomb correlated system. As the field increases, the tunneling conductance increases such that a very clear correlation between conductivity and density of states is found. Hall measurements show a striking field dependence of the hall coefficient with $1/R_h$ collapsing to zero at the metal insulator transition as well.

A number of experimental findings are noteworthy. First, the negative MR observed in these systems continues to 20T without showing signs of saturation. This is especially surprising since Gd is a trivalent $4f^7 5d^1 6s^2$ atom which is characterized by $J=S=7/2$ and $L=0$ due to the half filled f shell. Hence, no magnetic anisotropy

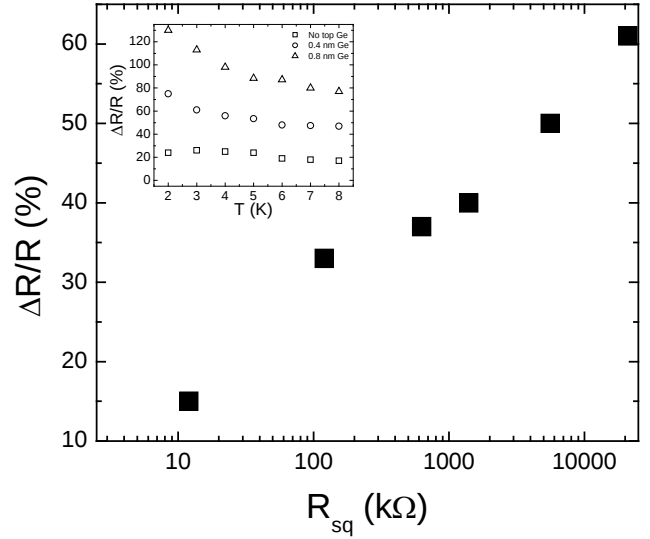


FIG. 1: Magnetoresistance magnitude ($\frac{R_0 - R_{9T}}{R_{9T}}$) as a function of sheet resistance for an uncoated Gd sub monolayer at $T=4\text{K}$ (In this sample the maximum resistance was attained at $H=0$). The insert shows the temperature dependence of $\Delta R/R$ in a different sample for the uncoated Gd (squares, $R_{sq}(4\text{K})=0.5\text{ M}\Omega$), an overlayer of $4\text{\AA}$ thick Ge (circles, $R_{sq}(4\text{K})=1.2\text{ M}\Omega$) and for an overlayer of $8\text{\AA}$ (triangles, $R_{sq}(4\text{K})=0.6\text{ M}\Omega$). Note that the temperature dependence becomes more pronounced with overlayer thickness.

is expected for the Gd ions and the magnetoresistance is expected to saturate at a relatively low magnetic field. Secondly, magnetization measurement show that the moment in these alloys is usually smaller than $7/2$ [8]. It peaks at the metal insulator transition (MIT) where it approaches the bulk value of $7/2$ but on both sides of the transition it is substantially reduced. These two findings lead to the speculation that there is an antiferromagnetic coupling between the Gd atoms and the surrounding semiconducting atoms [9] leading both to the lack of high field saturation and to the reduced net moment. The peak at the MIT is still not understood.

Very little has been explored in two dimensions along

these lines. In this paper we describe an experiment performed on a sub mono-atomic layer of Gd grown on an amorphous Ge or Sb substrate. We present MR data of this film. In addition, we study the change in the MR as we subsequently deposit an overlayer of amorphous Ge or Sb, *in-situ*. We find that there are large differences between an uncoated Gd sub monolayer system and one which is coated by an overlayer. The results demonstrate the important role played by the semiconductor surroundings on the magnetic properties of the ferromagnetic-semiconductor system.

The samples described in this paper were prepared by quench condensation i.e. sequential evaporation on a cryogenically cold substrate under UHV conditions while monitoring the film thickness and resistance. It is well established that if a metallic material is quench-condensed on a substrate that is pre-coated by an ultra-thin buffer layer of amorphous Ge or Sb, the sample grows rather uniformly and is electrically continuous at a thickness of 1-2 monolayers of material[10]. This is in contrast with the growth without a buffer layer in which case the film grows in a granular morphology [11, 12, 13]. The quench condensation method provides a very sensitive control on the sample growth process, allowing one to terminate the evaporation at any desired stage of the material deposition and "freeze" the morphological configuration. In particular, this technique allows one to stop the film growth at a thickness for which a measurable conductivity first appears across the sample. Hence one can grow an ultrathin layer which is electrically continuous but geometrically it is still a sub-monolayer. At $T=0$ we expect such monolayers to be insulating. In the current work we prepared the samples by growing a $10\text{\AA}$ thick Ge or Sb buffer-layer on a Si/SiO substrate at $T=5\text{K}$. Then we quench condensed an ultrathin layer of Gd ($3\text{-}4\text{\AA}$ thick) until a sheet resistance of a few $\text{M}\Omega$ was measured across the sample. We then added sequential sub monolayers of Gd thus reducing the sheet resistance, R_{sq} , in a controlled fashion. Finally, we coated the Gd by overlayers of the amorphous semiconductor material (Ge or Sb). Throughout the experiment we measured the transport (R - T) and magnetoresistance (R - H) properties for each evaporated layer. Magnetic field was applied perpendicular to the film. All measurements were performed in a shielded room and we ensured that the I-V characteristics of all films were in the ohmic regime.

We have studied 9 sets of samples of Gd-Sb and Gd-Ge, all of these samples exhibit similar behavior. The uncoated Gd sub-atomic layers on a semiconductor substrate exhibit negative MR which persist to 9 tesla without saturation. We observe amplitudes of the MR ($\frac{R_0 - R_{9T}}{R_{9T}}$) up to a factor of 60% at $T=2\text{K}$, decreasing monotonically as Gd is added to the layer, thus reducing R_{sq} (see figure 1). This is similar to the behavior in the 3D alloys in which the MR magnitudes decreases as the Gd concentration is increased. However, the 2D

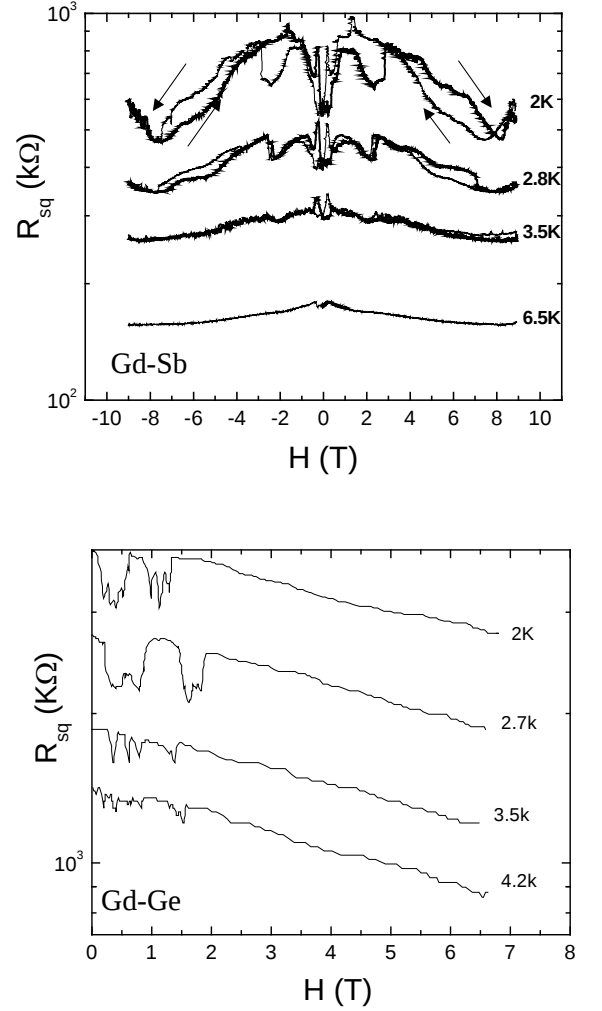


FIG. 2: Magnetoresistance traces of uncoated Gd sub monolayers on amorphous Sb (top) and Ge (bottom) for different temperatures. The top frame shows MR for both magnetic field sweep directions. Solid lines are for sweeps from left to right and dotted lines are for sweeps from right to left. The hysteretic nature of the traces is obvious.

samples show a number of unique properties. The temperature dependence of the MR in the uncoated Gd layer at $H=9\text{T}$ often tends to saturate as the temperature is reduced below $T=4\text{K}$ as demonstrated in figures 1 and 2 (left panel). In addition, a sample dependent structure is superimposed on the usual smooth negative MR background. This can be seen in figure 2 which shows a very profound detailed and hysteretic MR trace. The curves trace each other when sweeping the field in the same direction many times but they produce hysteretic mirror images when sweeping the field in opposite directions. The structure persists, in many cases, up to a field of

9T (the highest available field in our experiment). This is very surprising since a hysteretic MR trace is associated with magnetic anisotropy and preferred magnetic moment orientation. Since Gd is believed to be spherical, any anisotropy is expected to be negligible and its effect is expected to be limited to very small magnetic fields. This is clearly not the case for the results shown in figure 2 where the hysteretic sharp structure persists to at least several tesla and to at least 4.2K. None of this hysteresis is observed in 3 dimensions.

As the Gd layer is subsequently coated by an overlayer of Ge or Sb a number of clear trends are observed. The initial layers of the semiconductor overlayer (up to a thickness of $\sim 4\text{\AA}$) cause both the resistance and the MR to increase. Additional Ge or Sb overlayer evaporation causes the resistance to then decrease, however the MR continues to increase (we have observed $\frac{\Delta R}{R}$ values up to a factor of 5 at 9T) until, for thick enough overlayers (thicker than approximately $10\text{\AA}$), $\frac{\Delta R}{R}$ does not change with additional overlayer. In addition, the overlayers of Ge or Sb suppress the hysteretic structure and eventually yield smooth negative MR curves as demonstrated in figure 3. Another striking effect of the semiconductor overlayer is associated with the temperature dependence of the resistance. Figure 4 shows the transport properties of a Gd-Ge sample for uncoated Gd and two overlayer thicknesses for $H=0$ and $H=9\text{T}$. It is seen that the R-T curves can loosely fit a $\sigma = c \cdot T$ dependence in this temperature range. The slope, c , changes as a function of the overlayer thickness so that the R-T curves cross each other at various temperatures. This is very different than the behavior in the 3D case where the temperature dependence becomes weaker (monotonically) as the resistance decreases. In the 2D case, the observed crossing of the R-T traces implies that the overlayer material modifies the conduction mechanism leading to a qualitatively different temperature dependence.

The non-monotonic dependence of the resistance with overlayer thickness is peculiar. Naively, all other thing being unchanged, one would expect that adding a semiconductor between the Gd atoms would decrease the resistance because of the decrease in the tunneling barrier heights between the metallic atoms. This is indeed observed for thicker overlayers. The fact that the resistance increases for initial overlayer thicknesses implies that there is another competing mechanism. The observation that adding the overlayer is accompanied by a significant increase in MR amplitudes (for both regions of resistance change) leads us to speculate that the increase of resistance in the first overlayer stages is associated with an increase in magnetic disorder. We envision that the uncovered Gd atoms are forced to be oriented perpendicular to the substrate. The chemical bond of the Gd atom to the substrate semiconductor breaks the natural magnetic symmetry of the ion and orients the moment perpendicular to the substrate. Ferromagnetic

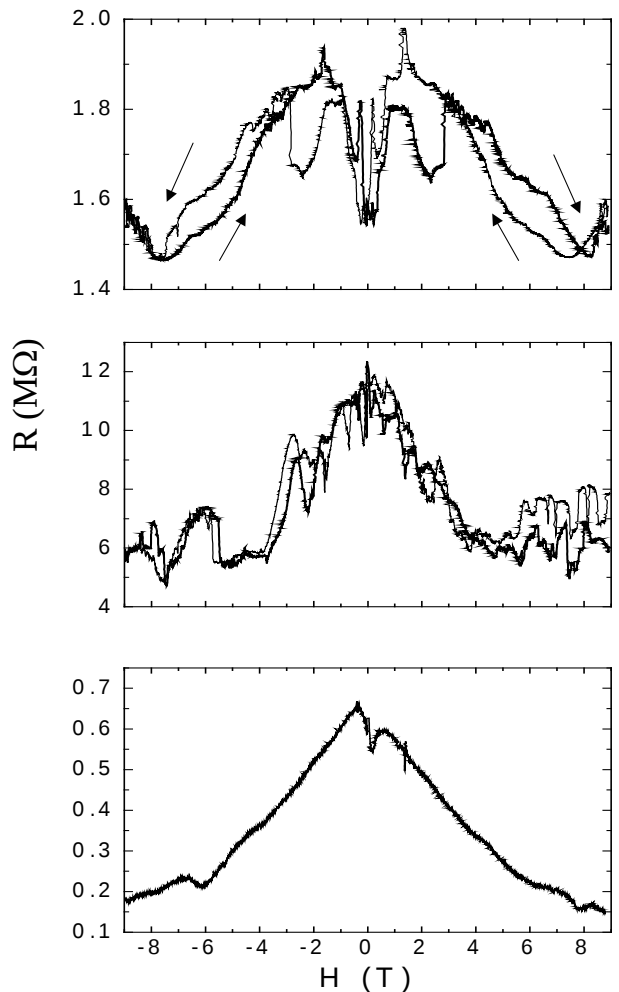


FIG. 3: Magnetoresistance curves of the Gd-Sb sample of figure 2 for the uncoated layer (top), a $5\text{\AA}$ thick Sb overlayer (middle) and a $9\text{\AA}$ thick Sb overlayer (bottom).

interactions between the Gd atoms create magnetic domains which are either "up" or "down" on the surface. In this picture, aside from the up/down disorder, much of the magnetic disorder, which characterizes the 3D alloys and dominates their MR behavior, is quenched in the 2D sub-mono-atomic films because the Gd atoms moments are confined to being vertical. The subsequent semiconductor overlayer relaxes this constraint and allows the magnetic moment to splay into all the 3D space. This increases the magnetic disorder leading to an increase both in the resistance and in the MR. It appears therefore that there are two conflicting effects of the top semiconducting layer. The generation of parallel tunneling paths acts to raise the conductivity and the increase of magnetic disorder acts to reduce conductivity. The latter

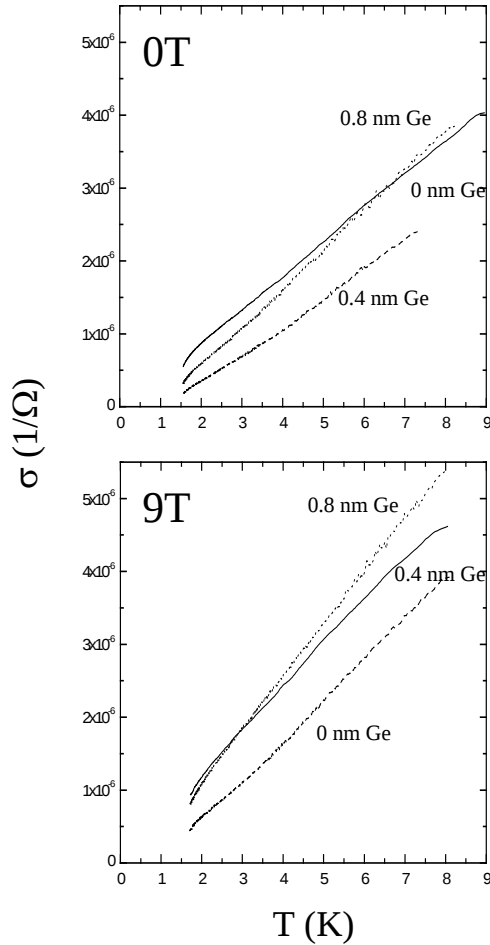


FIG. 4: Conductivity as a function of temperature for a Gd-Ge sample at $H=0T$ (top panel) and $H=9T$ (bottom panel). Solid lines are for the uncoated Gd layer, dashed lines are for a 4Å thick Ge overlayer and dotted lines are for a 8Å thick Ge overlayer.

effect is highly dependent on temperature as observed in the 3D alloy case, while tunneling effects are relatively temperature insensitive. This may explain the unique temperature dependence of the resistance as an overlayer is added to the Gd film (figure 4). At high temperatures the main effect of the semiconducting layer is to increase the tunneling conductance, while at low temperatures the dominant factor is the enhancement of disorder which decreases conductivity. This leads to the crossing of the R-T curves as a function of overlayer thickness which is observed in figure 4.

The above picture can also explain the evolution of the structure observed in the MR (figure 3). The hysteretic structure is a consequence of the anisotropy in the Gd atoms on the surface. In the absence of magnetic field, domains are randomly oriented up or down. With the application of a perpendicular field, the domains orient with the field direction. Each flip of a domain mo-

ment will cause a sharp resistance change (which may be an increase or decrease depending on the microscopic configuration). The presence of an overlayer relaxes the symmetry and restores the isotropic nature of the Gd. In effect, coating the Gd with amorphous Ge or Sb causes a crossover from a 2D magnetic disorder to a 3D magnetic disorder. This leads to suppression of the hysteretic structure because in the 3D disorder the moments can rotate continuously, without abrupt orientation flips, until they align with the field.

In summary, the magnetic properties of a 2D sub monolayer of Gd on an amorphous semiconducting substrate show a number of features which are different than the 3D alloys. These include a relatively small magnitude of MR, small temperature dependence and a hysteretic fine-structure superimposed on the MR curves. When these layers are covered by a semiconducting overlayer, the samples evolve towards behavior which is more characteristic of 3D alloys, i.e. the MR and its temperature dependence becomes larger and the fine-structure vanishes. These results lead us to suggest that the coated layers are the limiting case of a very thin Gd-Ge alloy and share similar physics while the uncoated layers exhibit qualitatively different results due to the fact that the magnetic disorder in these samples is substantially reduced.

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